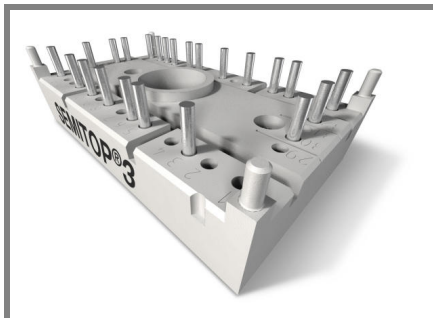


# SK150GB066T



SEMITOP® 3

## IGBT Module

SK150GB066T

### Target Data

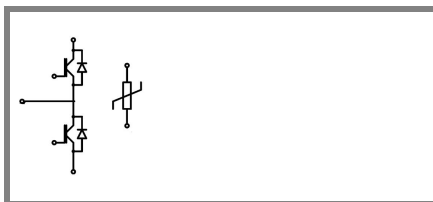
### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL HD technology FWD
- Integrated NTC temperature sensor

### Typical Applications\*

### Remarks

- $V_{isol} = 3000V$  AC, 50Hz, 1s

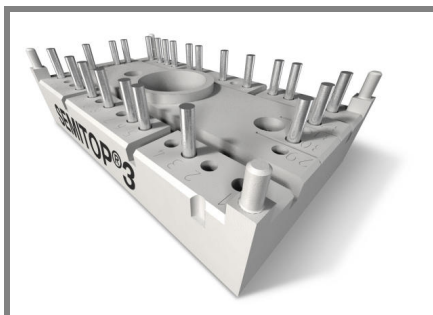


GB-T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$	$T_j = 25\text{ °C}$	600		V
$I_C$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	124	A
		$T_s = 70\text{ °C}$	96	A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	300		A
$V_{GES}$		± 20		V
$t_{psc}$	$V_{CC} = 360\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 150\text{ °C}$ $V_{CES} < 600\text{ V}$	6		µs
<b>Inverse Diode</b>				
$I_F$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	135	A
		$T_s = 70\text{ °C}$	95	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	300		A
<b>Module</b>				
$I_{t(RMS)}$				A
$T_{vj}$		-40 ... +175		°C
$T_{stg}$		-40 ... +125		°C
$V_{isol}$	AC, 1 min.	2500		V

Characteristics		$T_s = 25\text{ °C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2,4\text{ mA}$	5	5,8	6,5	V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$	0,0076		mA
		$T_j = 125\text{ °C}$			mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$	1200		nA
		$T_j = 125\text{ °C}$			nA
$V_{CE0}$		$T_j = 25\text{ °C}$	0,8	1,1	V
		$T_j = 150\text{ °C}$	0,7	1	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	4	5	mΩ
		$T_j = 150\text{ °C}$	6,35	7	mΩ
$V_{CE(sat)}$	$I_{Cnom} = 150\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,45	1,85	V
		$T_j = 150\text{ °C}_{chiplev.}$	1,65	2,05	V
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	9,4		nF
$C_{oes}$			0,6		nF
$C_{res}$			0,29		nF
$Q_G$	$V_{GE} = -7V...+15V$	1400		nC	
$t_{d(on)}$	$R_{Gon} = 8\text{ }\Omega$ $di/dt = 2250\text{ A}/\mu\text{s}$	$V_{CC} = 300V$ $I_C = 150A$	95		ns
$t_r$			50		ns
$E_{on}$			6,25		mJ
$t_{d(off)}$	$R_{Goff} = 8\text{ }\Omega$ $di/dt = 2250\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$ $V_{GE} = -7/+15\text{ V}$	541		ns
			70		ns
$E_{off}$			5,7		mJ
$R_{th(j-s)}$	per IGBT	0,65		K/W	

# SK150GB066T



**SEMITOP<sup>®</sup> 3**

## IGBT Module

**SK150GB066T**

Target Data

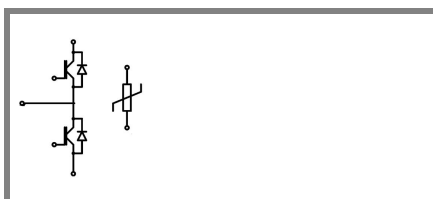
### Features

- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL HD technology FWD
- Integrated NTC temperature sensor

### Typical Applications\*

### Remarks

- $V_{isol} = 3000V$  AC, 50Hz, 1s

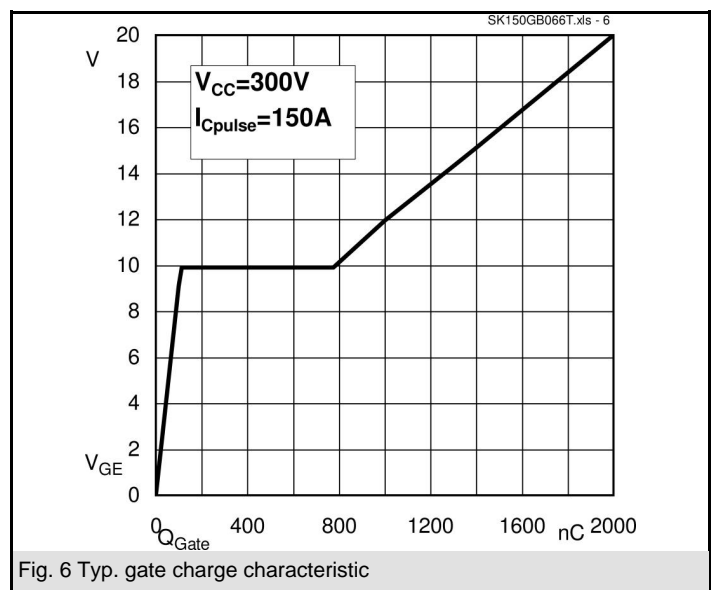
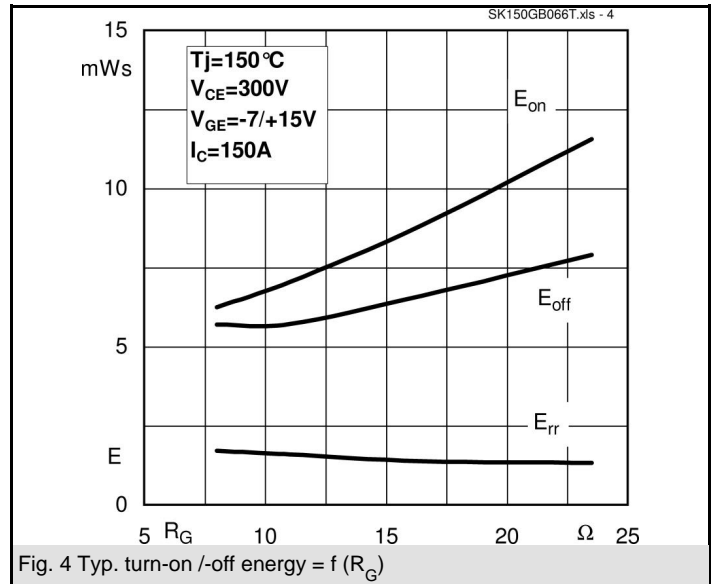
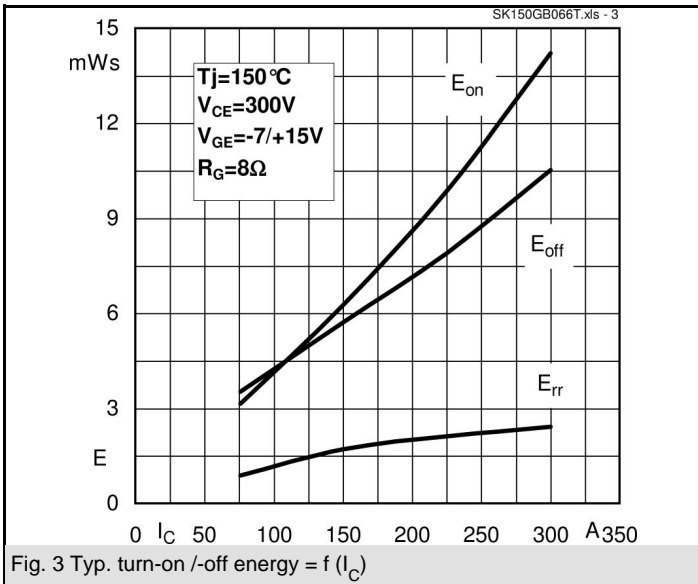
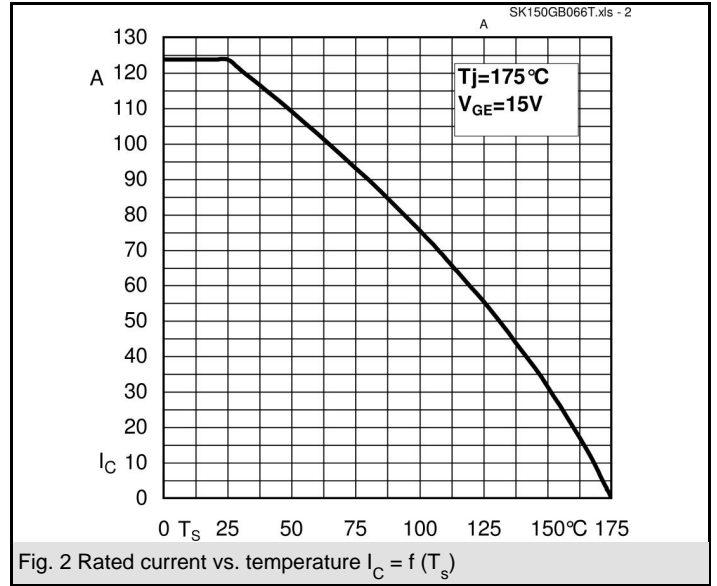
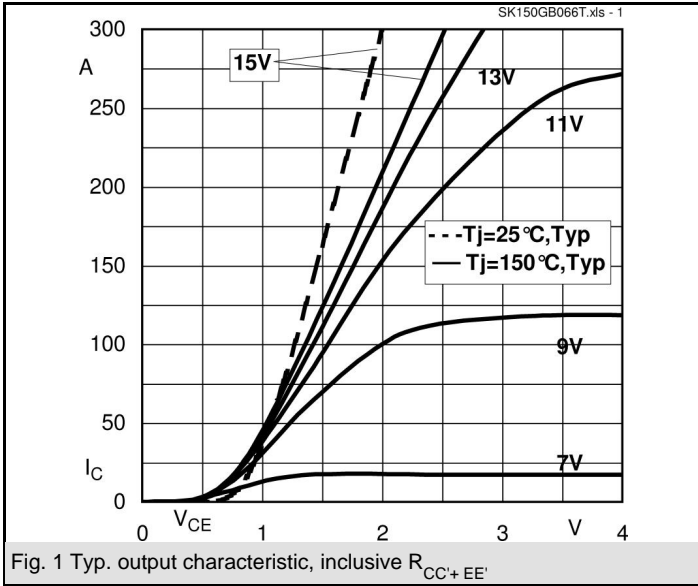


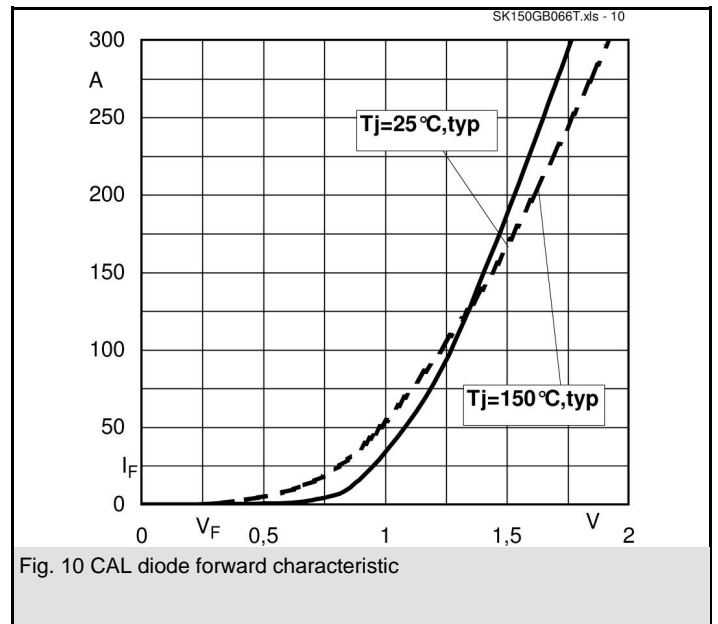
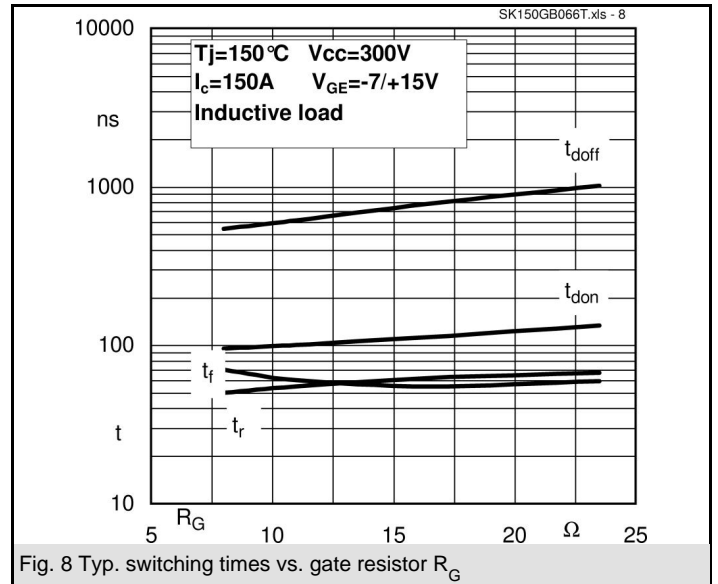
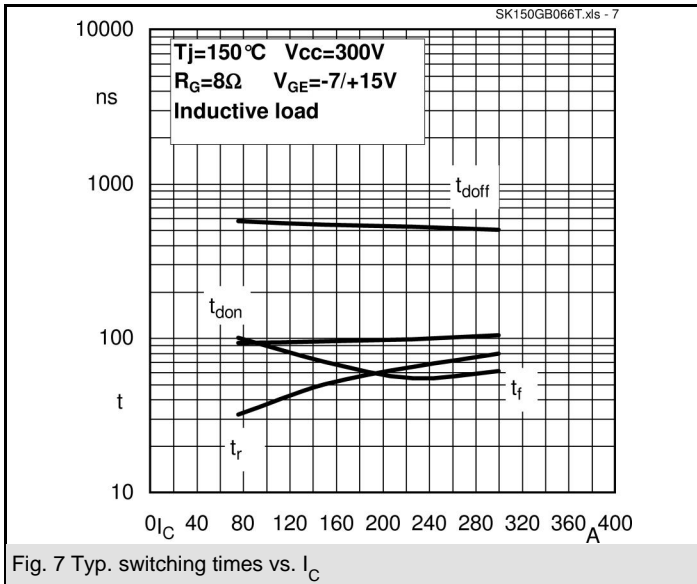
**GB-T**

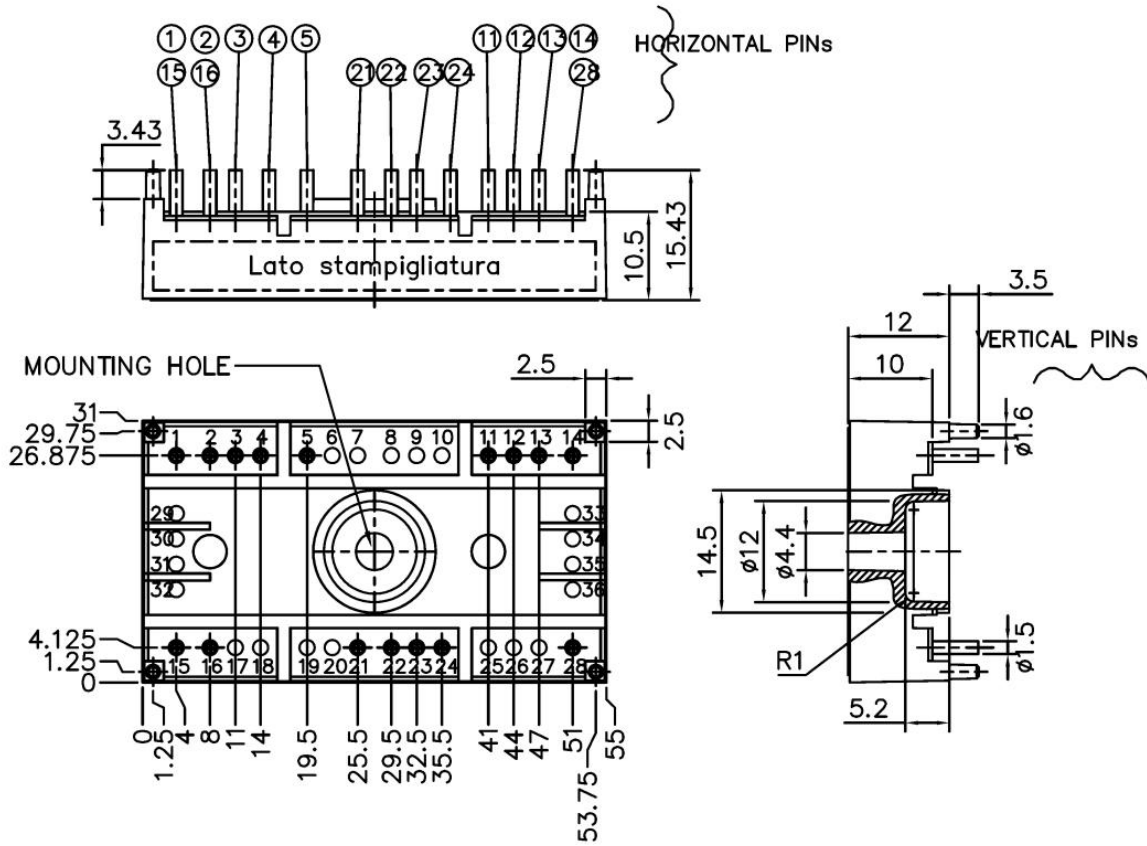
Characteristics		min.	typ.	max.	Units
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 150 A; V_{GE} = 0 V$		1,35		V
			1,31		V
$V_{F0}$			0,85		V
$r_F$			3,9		mΩ
$I_{RRM}$	$I_F = 150 A$		100		A
$Q_{rr}$	$di/dt = 2250 A/\mu s$		11		μC
$E_{rr}$	$V_{CC} = 300V$		1,7		mJ
$R_{th(j-s)D}$	per diode		0,73		K/W
$M_s$	to heat sink	2,5		2,75	Nm
w			60		g
<b>Temperature sensor</b>					
$R_{100}$	$T_s = 100^\circ C (R_{25} = 5k\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

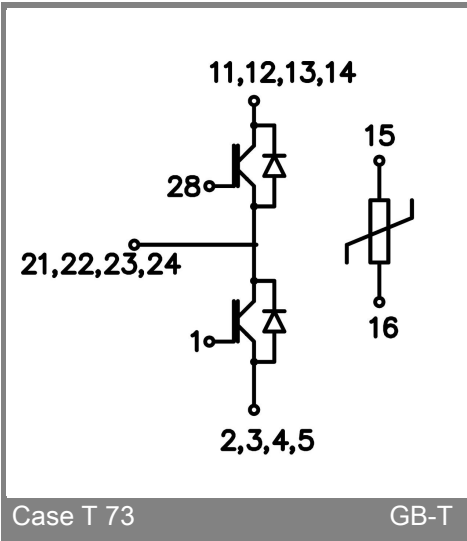
\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T73 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 73

GB-T